

TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SB1667(SM)

Audio Frequency Power Amplifier Applications

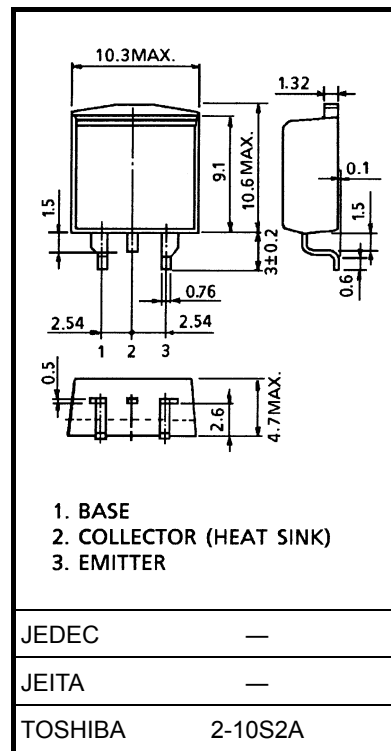
Unit: mm

- Low saturation voltage: $V_{CE(sat)} = -1.7\text{ V (max)}$
($I_C = -3\text{ A}$, $I_B = -0.3\text{ A}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

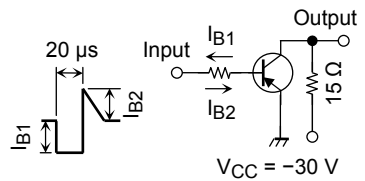
| Characteristics | Symbol | Rating | Unit |
|-----------------------------|-----------|--------------------------|------------------|
| Collector-base voltage | V_{CBO} | -60 | V |
| Collector-emitter voltage | V_{CEO} | -60 | V |
| Emitter-base voltage | V_{EBO} | -7 | V |
| Collector current | I_C | -3 | A |
| Base current | I_B | -0.5 | A |
| Collector power dissipation | P_C | $T_a = 25^\circ\text{C}$ | 1.5 |
| | | $T_c = 25^\circ\text{C}$ | 25 |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -55 to 150 | $^\circ\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



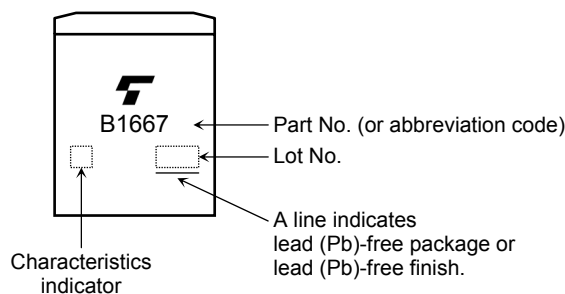
Weight: 1.4 g (typ.)

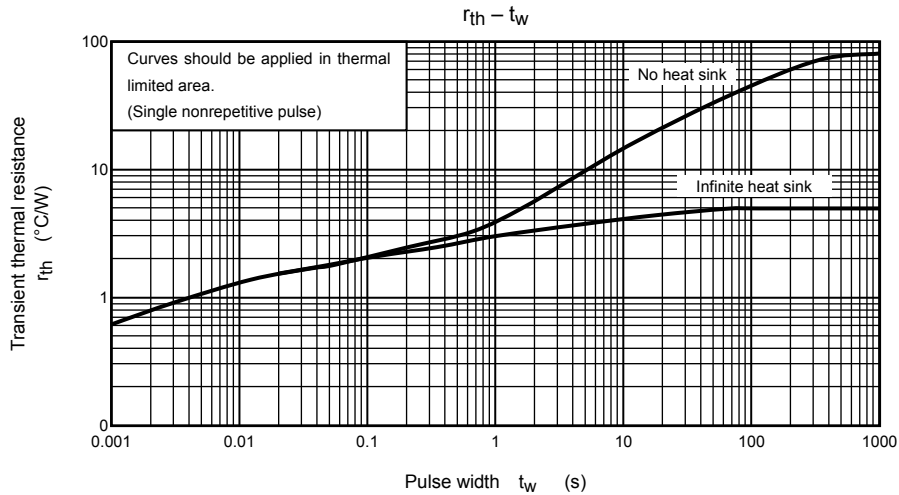
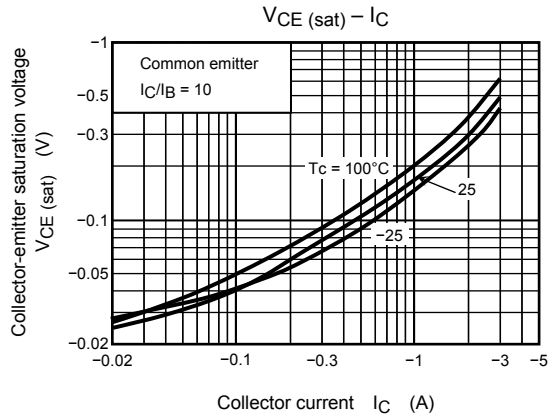
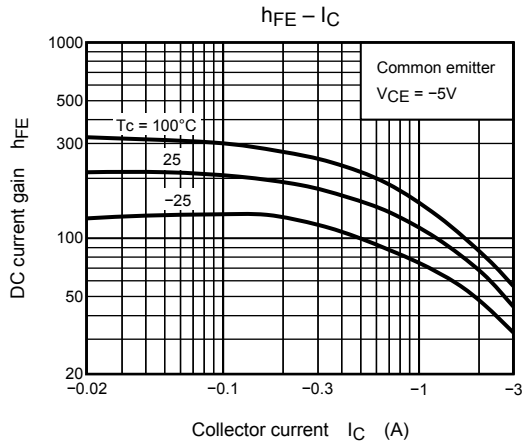
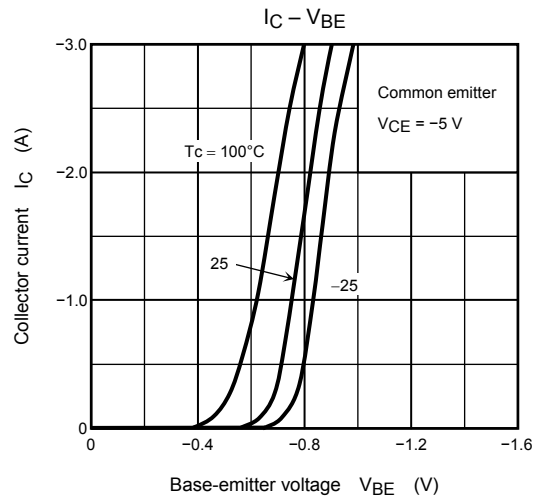
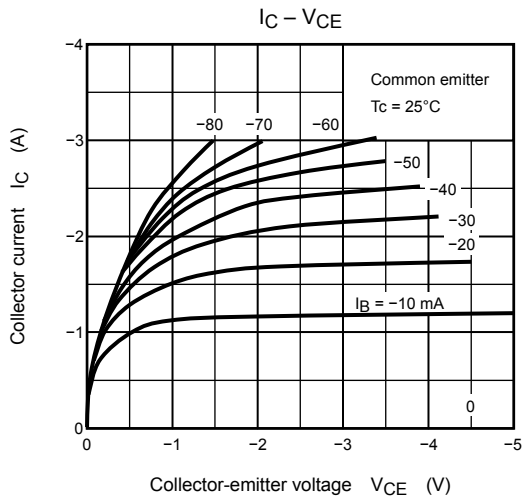
Electrical Characteristics (Ta = 25°C)

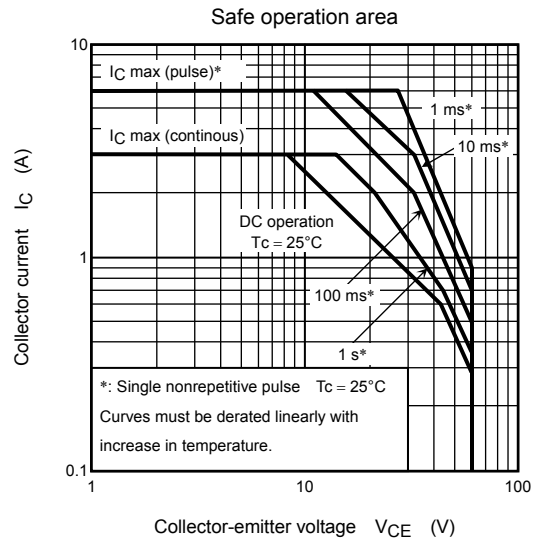
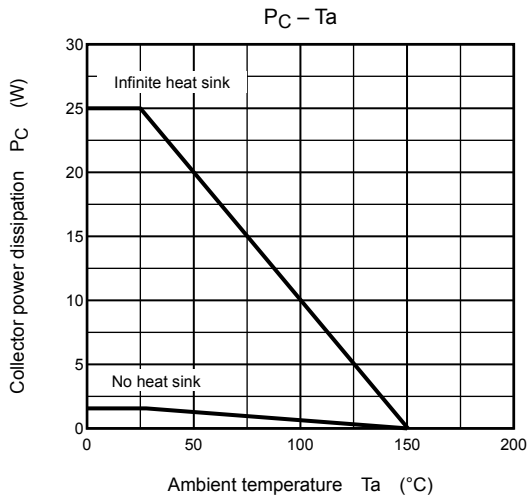
| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------------|-----------------------|---------------|--|-----|------|------|---------------|
| Collector cut-off current | | I_{CBO} | $V_{CB} = -60\text{ V}, I_E = 0$ | — | — | -100 | μA |
| Emitter cut-off current | | I_{EBO} | $V_{EB} = -7\text{ V}, I_C = 0$ | — | — | -100 | μA |
| Collector-emitter breakdown voltage | | $V_{(BR)CEO}$ | $I_C = -50\text{ mA}, I_B = 0$ | -60 | — | — | V |
| DC current gain | $h_{FE(1)}$ (Note) | | $V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}$ | 60 | — | 300 | |
| | $h_{FE(2)}$ | | | | | | |
| Collector-emitter saturation voltage | | $V_{CE(sat)}$ | $I_C = -3\text{ A}, I_B = -0.3\text{ A}$ | — | -0.5 | -1.7 | V |
| Base-emitter voltage | | V_{BE} | $V_{CE} = -5\text{ A}, I_C = -0.5\text{ A}$ | — | -0.7 | -1.0 | V |
| Transition frequency | | f_T | $V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}$ | — | 9 | — | MHz |
| Collector output capacitance | | C_{ob} | $V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$ | — | 150 | — | pF |
| Switching time | Turn-on time | t_{on} |  <p style="text-align: center;">$V_{CC} = -30\text{ V}$</p> <p style="text-align: center;">$-I_{B1} = I_{B2} = 0.2\text{ A}, \text{duty cycle} \leq 1\%$</p> | — | 0.4 | — | μs |
| | Storage time | t_{stg} | | — | 1.7 | — | |
| | Fall time | t_f | | — | 0.5 | — | |

Note: $h_{FE(1)}$ classification O: 60 to 120, Y: 100 to 200, GR: 150 to 300

Marking







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20070701-EN

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